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Wide Band-Gap Devices for Solid State Transformer Applications

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□ Challenges of Solid State Transformer

- Concept of Solid State Transformer
- System Requirements of Solid State Transformer

□ Opportunities of WBG Devices for SST Applications

- Advantages of WBG devices
- Early adoption of WBG devices for SST





Advantages

- Highly robust / Reliable
- Highly efficient (98.5%...99.5%)
- Relatively inexpensive

Weaknesses

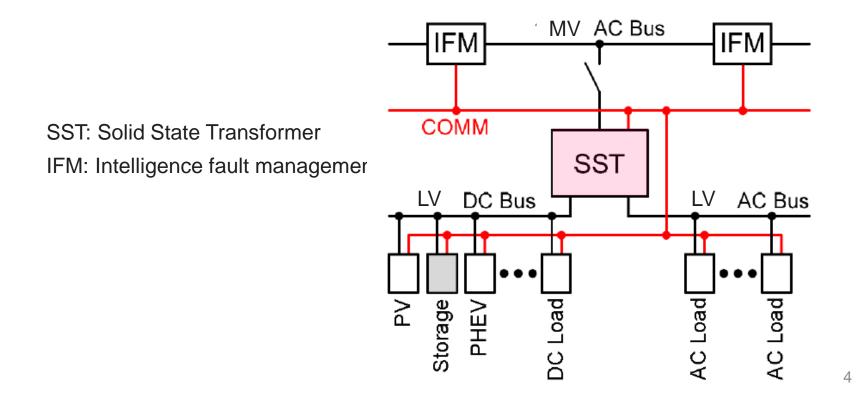
- No capability of voltage/ frequency regulation
- Large Weight / Volume







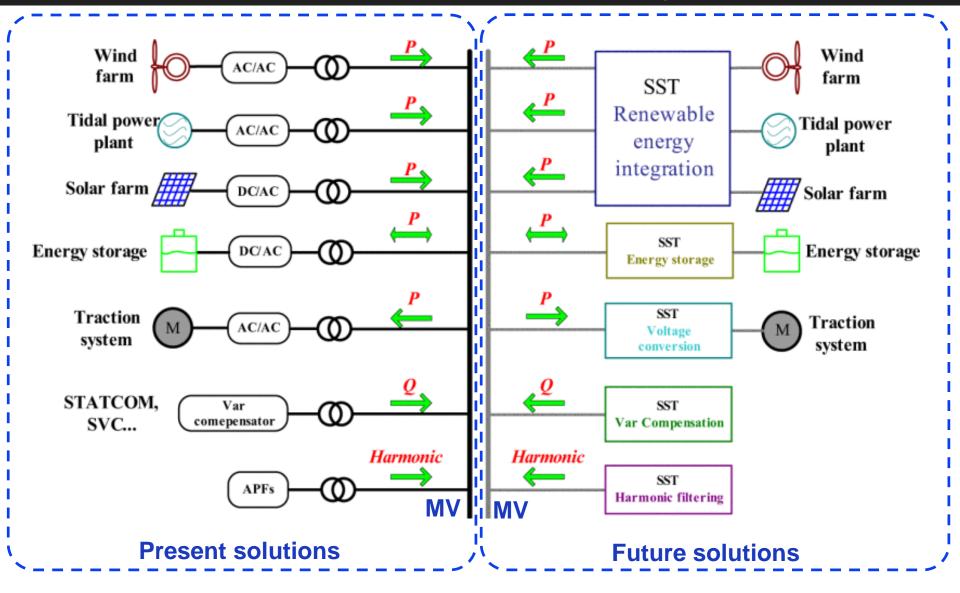
- DC and/or AC interfaces with high frequency isolation between medium voltage grid and Renewable Energy Resources, Distributed Energy Storage, Electric Vehicles, and DC or AC loads
- A platform enables uni- or bi-directional power flow with Local Autonomous Control and Distributed Intelligence through Communications





Potential Applications of SST in Future Distribution System





Reference: Xu, She, etc, Review of Solid-State Transformer Technologies and Their Application in Power Distribution Systems



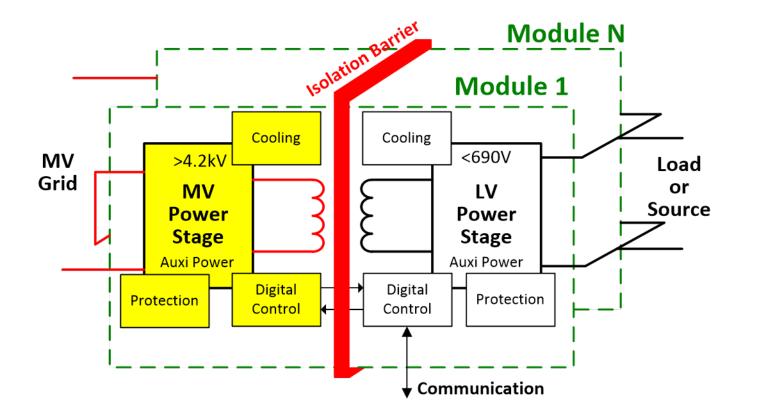


Modularized design

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- Voltage/current balancing
- High efficiency topology
- Packing & cooling

- Control & communication
- Redundancy & reliability
- □ High voltage isolation
- Grounding & protection

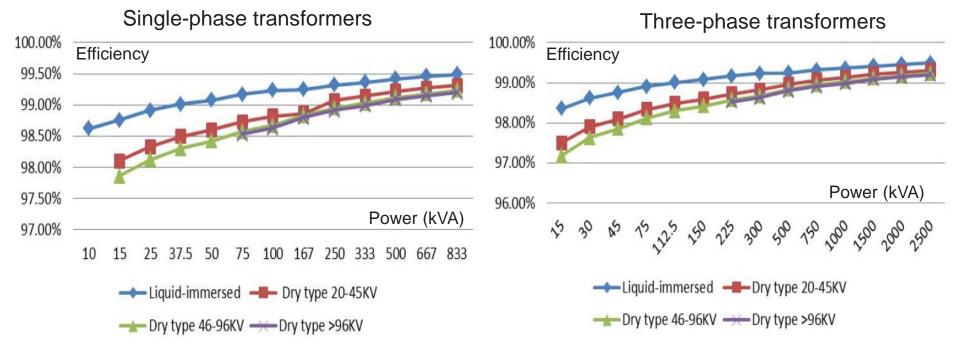






- The overall efficiency of the distribution transformer required by the standard is >97% irrespective of power rating
- □ Big efficiency challenge for MV and LV power stage plus isolation in the SST

Distribution transformer national efficiency standards of U.S.A

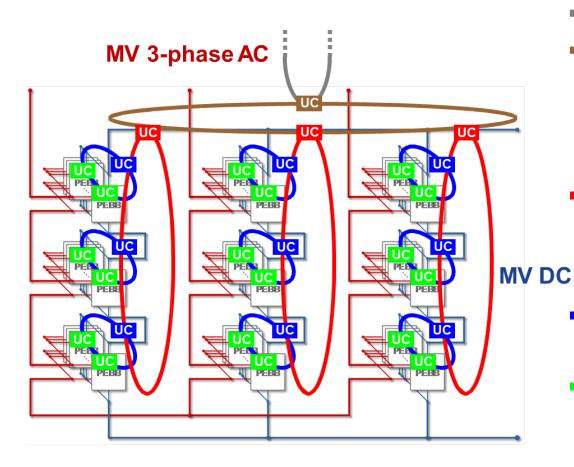


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Distributed Hierarchical Control



Scalable PEBB-based converter

- Mission Control
- Converter Control
 - Multi-phase coordination
 - Application specific control

Stacking Control

- Voltage balancing
- Output voltage / current control
- Paralleling Control
 - Current balancing

PEBB Control

- Gate signal generation
- Local high frequency control (> f_{sw})
- Fast local protection







Outline



Challenges of Solid State Transformer

- Concept of Solid State Transformer
- System Requirements of Solid State Transformer

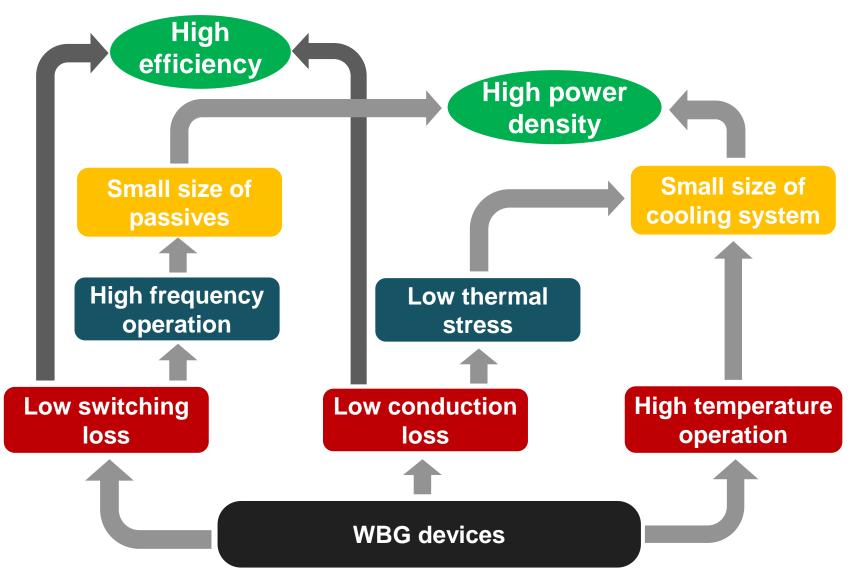
Opportunities of WBG Devices for SST Applications

- Advantages of WBG devices
- Early adoption of WBG devices for SST



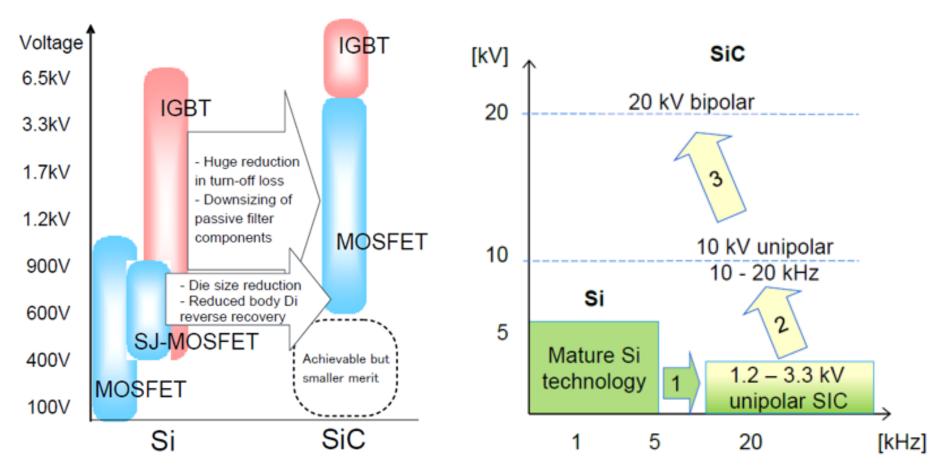
Why WBG Semiconductors ?











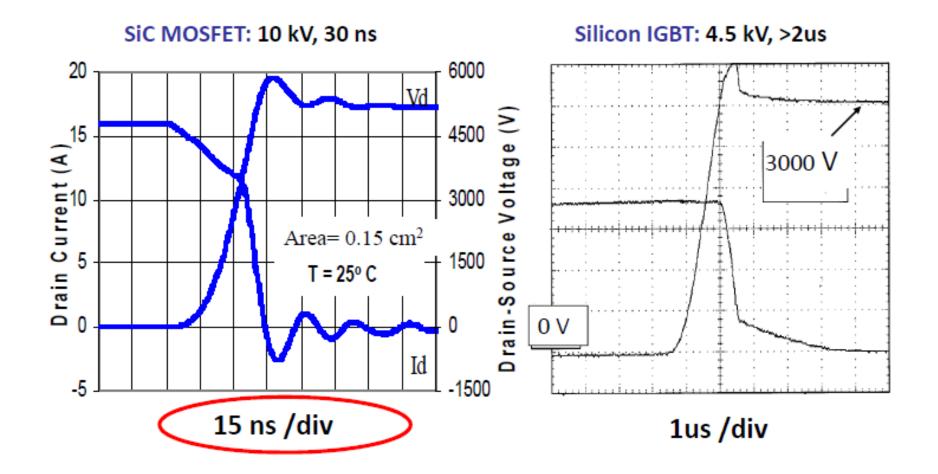
Reference: Peter K. Steimer, ABB, MV WBG Power Electronics for Advanced Distribution Grids, NIST/DOE Workshop, April 15, 2016

Reference: Rohm website

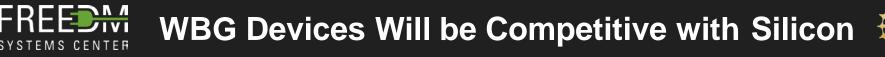


High Switching Speed at High Voltage of SiC MOSFET

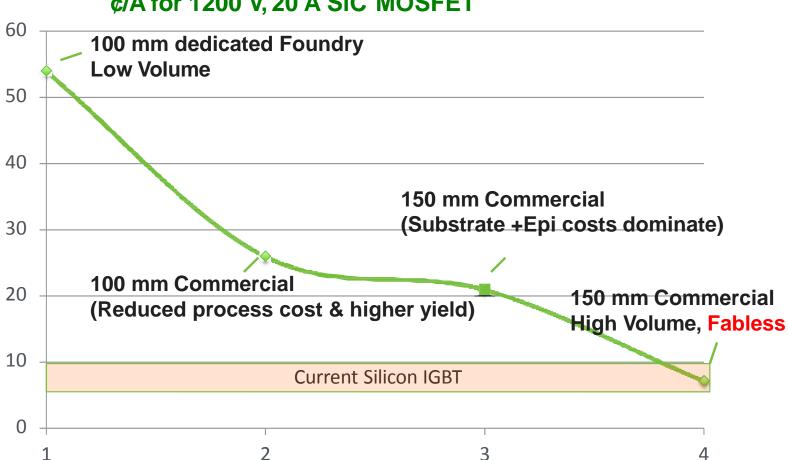




A. Hefner, et.al. "Recent Advances in High-Voltage, High-Frequency Silicon-Carbide Power Devices," IEEE IAS Annual Meeting, October 2006



□ Price of SiC switches will be at ~10 Cents/Amp possibly in 3-4 years



¢/A for 1200 V, 20 A SiC MOSFET

Reference: Anant Agarwal, Wide Bandgap Device Manufacturing, NIST/DOE Workshop, April 15, 2016 16







Challenges of Solid State Transformer

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- **Opportunities of WBG Devices for SST Applications**
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AC/AC SST Using 13kV SiC Mosfets for Power Substation



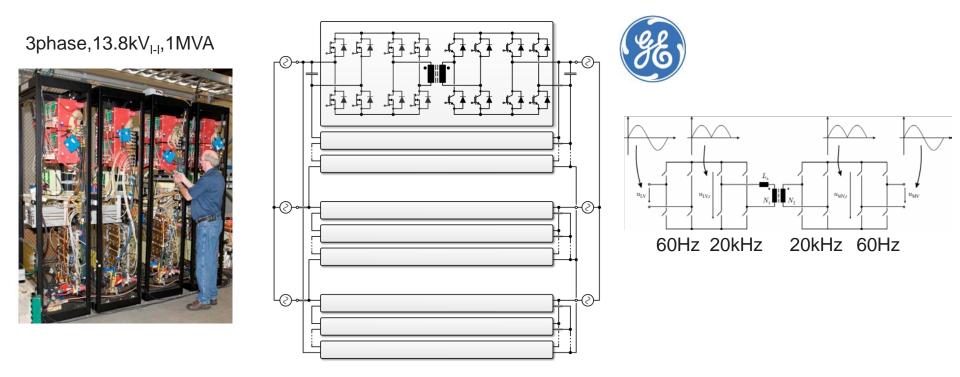
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□ Key technologies

- ✓ Power device: 13kV, 120A SiC half-bridge MOSFET modules
- Single-stage AC-AC topology: Only one-stage operates at 20kHz MF to control the voltage

□ Comparison between this SST solution and the conventional 50/60 Hz transformer

- ✓ Potential smart grid application because of the voltage controllability
- ✓ 1.3X weight reduction and 2X volume reduction with 97% total efficiency



M. K. Das, C. Capell, D. E. Grider, S. Leslie, J. Ostop, R. Raju, M. Schutten, J. Nasadoski, and A. Hefner, "13kV, 120A SiC half H-bridge power MOSFET modules suitable for high frequency, medium voltage applications," in Proc. IEEE ECCE, Sept. 2011.



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AC/DC SST Using 1.7kV SiC for Data Center: Boost Power Stage on LV Side

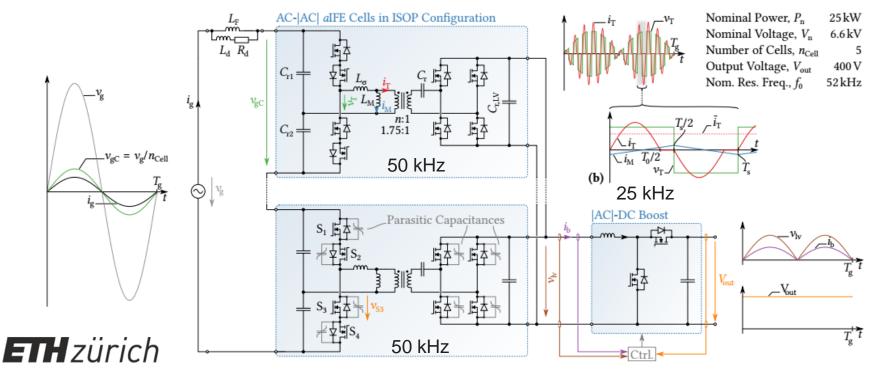


□ Key technologies

- ✓ **Power device:** 1700V/45mOhm SiC MOSFET, 5 cells in series for MV; 900V/11.5mOhm SiC for LV
- Topology: LLC resonant AC-DC with fixed gain + LV boost dc-dc
- ✓ The simplest high-voltage-side topology and the simplest system-level control

Comparison between this SST solution and the conventional 50/60 Hz transformer + LV PFC converter

✓ 1-2% efficiency improvement and significant size/weight reduction



J. E. Huber, D. Rothmund, L. Wang, and J. W. Kolar, "Full-ZVS modulation for all-SiC ISOP-type isolated front end (IFE) solid-state transformer," in Proc. IEEE ECCE, Sep. 2016.



AC/DC SST Using 1.2 kV SiC & 650V GaN for Data Center: Boost Power Stage on MV Side

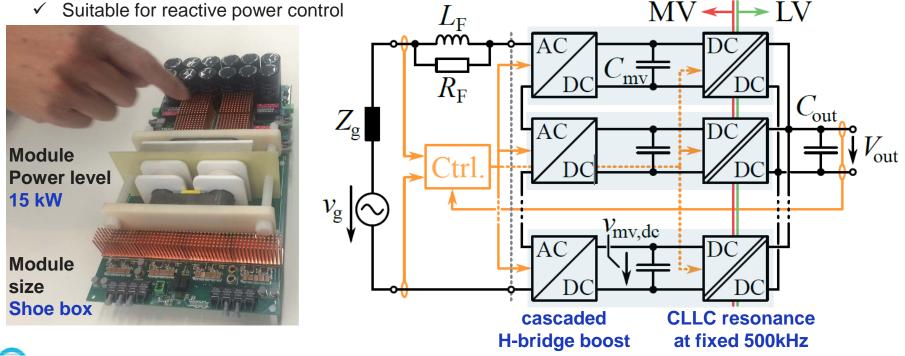


□ Key technologies

- ✓ **Power device:** 1200V/25mOhm SiC MOSFET, 4 cells in for 2.4kVrms; 650V/25mOhm GaN for LV
- ✓ **Topology**: cascaded H-bridge boost +CLLC resonant converter with **500kHz** fixed frequency

Comparison between this SST solution and the conventional 50/60 Hz transformer + LV PFC converter

- ✓ Significant size reduction because the transformer operating at 500 kHz
- ✓ Peak efficiency: 98%





Fred Lee, "Solid State Transformer for DC data center", PowerAmerica Annual Meeting, Jan. 18th, 2017



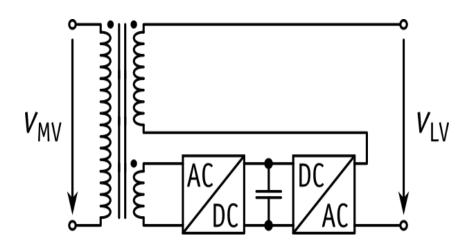


□ 3X cost reduction

- ✓ SST mixing LFT solution : **MV partial power SST + high power LF transformer**
- ✓ This SST do NOT process the full power flow, which results in significant cost saving vs. normal SST

□ Comparison between this SST solution and the conventional 50/60 Hz transformer

- ✓ Good candidate for future smart grid application
- ✓ Combining controllability of SST and low cost of LF transformer
 - Voltage scaling & galvanic isolation
 - Correction of voltage sags, unbalances and phase angle errors
- Reactive power compensation
- Can be extended to bidirectional power flow control







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CREATING INNOVATIVE AND RELIABLE CIRCUITS USING INVENTIVE TOPOLOGIES AND SEMICONDUCTORS (CIRCUITS)





- Topologies and control methods that combine multiple functions (e.g. rectification and step-down) into one single topology with reconfigurable power flow paths
- EMI free MV circuit topologies, zero-voltage and/or current switching with minimum magnetics
- Power-over-fiber based gate drive with comprehensive protection functions for >10kV SiC power devices
- ✓ HV and reliable solid-state transformers (SST), circuit topologies capable of >1000 kW of power conversion
- ✓ Combined bi-directional ac-dc charger and dc-dc converter
- ✓ 480Vac 3 phase to ≥ 900Vdc converter, compact sub 2-minute EV charging stations with reduced installation cost

Thank You !

Any Suggestions or Questions ?

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